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**INFORMATION DISCLOSURE
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PTO/SB/06A(10-01)
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 US Patent & Trademark Office, U.S. DEPARTMENT OF COMMERCE

Complete if Known	
Application Number	Unknown 10/600 965
Filing Date	Even Date Herewith 6/20/03
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown 2813
Examiner Name	Tran, Mai-Huong

Sheet 1 of 2

Attorney Docket No: 303.716US2

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	Application Number	Unknown 10/600 965
	Filing Date	Even Date Herewith 6/20/03
	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown 2813
	Examiner Name	Tran, Mai-Huong
Sheet 2 of 2		Attorney Docket No: 303.716US2

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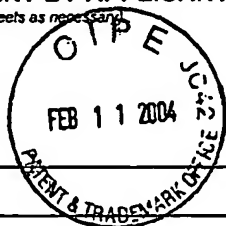
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<i>Complete if Known</i>	
Application Number	10/600965
Filing Date	June 20, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Tran, Mai-Huong

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